



# 제25회 한국반도체학술대회

The 25<sup>th</sup> Korean Conference on Semiconductors

2018년 2월 5일(월)-7일(수), 강원도 하이원리조트 컨벤션 호텔

2018년 2월 7일(수), 13:15-14:45

Room I (청옥II+III, 6층)

## K. Memory (Design & Process Technology) 분과

### [WI3-K] FeRAM and Transparent ReRAM

좌장: 김윤 교수(부산대학교), 이재구 박사(삼성전자)

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| <p><b>WI3-K-1</b><br/>13:15-13:30</p> | <p><b>Characterization of Ferroelectric Hafnium Oxide Thin Film</b><br/>Sang Hyun Sung<sup>1</sup>, Do Hyun Kim<sup>1</sup>, Il Suk Kang<sup>2</sup>, and Keon Jae Lee<sup>1</sup><br/><i><sup>1</sup>Department of Materials Sciences and Engineering, KAIST, <sup>2</sup>Nano Research Division, National NanoFab Center</i></p>  |
| <p><b>WI3-K-2</b><br/>13:30-13:45</p> | <p><b>New Non-volatile Multi-level Cell Using Epitaxial Strain Effect and Double Ferroelectric Tunnel Junctions</b><br/>Moonhoi Kim, Junbeom Seo, and Mincheol Shin<br/><i>School of Electrical Engineering, KAIST</i></p>  |
| <p><b>WI3-K-3</b><br/>13:45-14:00</p> | <p><b>Improvement of ZnO Resistive Switching Devices by Metal Thin Layer on ITO Bottom Electrode for Transparent Devices</b><br/>Taehoon Lee<sup>1</sup>, Yong Chan Jung<sup>1</sup>, Sejong Seong<sup>1</sup>, Seon Yong Kim<sup>1</sup>, In-Sung Park<sup>1,2</sup>, and Jinho Ahn<sup>1,2</sup><br/><i><sup>1</sup>Division of Materials Science and Engineering, Hanyang University, <sup>2</sup>Institute of Nano Science and Technology, Hanyang University</i></p> |
| <p><b>WI3-K-4</b><br/>14:00-14:15</p> | <p><b>Investigation on Resistive Switching in Zn-Sn-O Film Using Microwave Irradiation</b><br/>Tae-Wan Kim and Won-Ju Cho<br/><i>Department of Electronic Materials Engineering, Kwangwoon University</i></p>   |
| <p><b>WI3-K-5</b><br/>14:15-14:30</p> | <p><b>Analysis of LRS Retention Fail based on Joule Heating Effect in InGaZnO RRAM</b><br/>Geumho Ahn, Jun Tae Jang, Daehyun Ko, Hyeri Yu, Haesun Jung, Jihyun Rhee, Hyun-Sun Mo, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim<br/><i>School of Electrical Engineering, Kookmin University</i></p>   |
| <p><b>WI3-K-6</b><br/>14:30-14:45</p> | <p><b>Capacitorless 1T-DRAM Device</b><br/>Sehyun Kwon<sup>1</sup>, Minho Choi<sup>1</sup>, In-sung Park<sup>2</sup>, Yong Tae Kim<sup>3</sup>, and Jinho Ahn<sup>1,2</sup><br/><i><sup>1</sup>Department of Materials Science and Engineering, Hanyang University, <sup>2</sup>Institute of Nano Science and Technology, Hanyang University, <sup>3</sup>KIST</i></p>  |